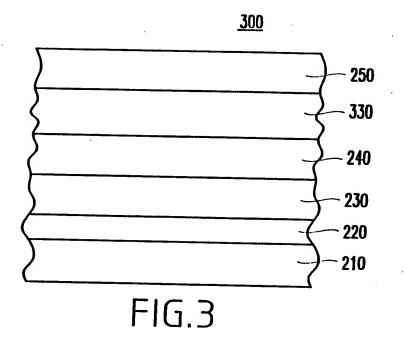


FIG.1



7.7 ·	414				
; ;			+ - + - +		1 1 1 1 1 1
			Start		2
			Optionally		
		1401 -	Optionally expose Oxicle/substrate to Oz benn		
			to Oz benm		
		14/12	Cool Oxide		
		1/42/2	Cool oxide On substrate		
:  -  -					<del>                                     </del>
	140			-	
		1403	Depositamorphous		
j			Semiconductor material on oxide		
l insque					
		1/10/1			
		1704	Gradually reat structure		
			in Oresence		
<b>1</b>			of flux/vapor of surfactant)		
			- Surficient		
		1405			,
	Hig.	14	DOTIONALLY EXPOSE OLIDER	1 1 1 1 1	
			expose oxide/ Substrate		
			to Oz beam		
					1.
		41	Optimally experie		
-		100	Optionally expose Synface to Atomic hydrogen beam		
ļ .			beam yourge		
			END		
	Missing a second of the second	in English States and Company of the Company			